

CXTA62
SURFACE MOUNT
PNP SILICON
DARLINGTON TRANSISTOR



SOT-89 CASE

CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXTA62 is a PNP Silicon Darlington transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

MARKING CODE: FULL PART NUMBER

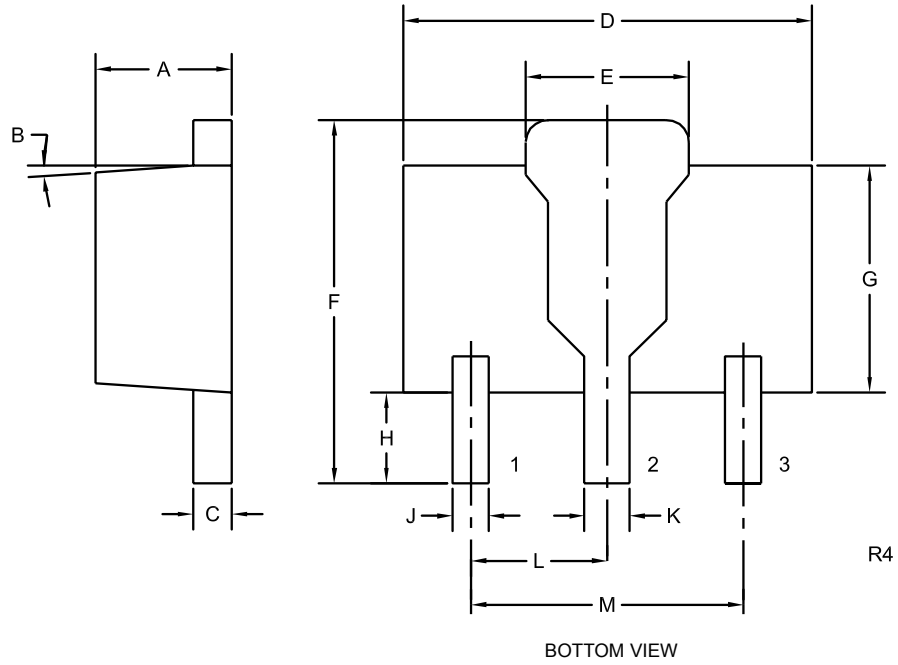
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CES}	20	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Power Dissipation	P_D	1.2	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	104	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=15\text{V}$			100	nA
I_{EBO}	$V_{EB}=10\text{V}$			100	nA
$B_{V_{CES}}$	$I_C=100\mu\text{A}$	20			V
$B_{V_{CBO}}$	$I_C=100\mu\text{A}$	20			V
V_{CESAT}	$I_C=10\text{mA}, I_B=10\mu\text{A}$			1.0	V
V_{BEON}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$			1.4	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	20K			

SOT-89 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

LEAD CODE:

- 1) EMITTER
- 2) COLLECTOR
- 3) BASE

MARKING CODE:

FULL PART NUMBER